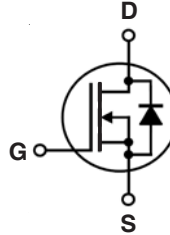
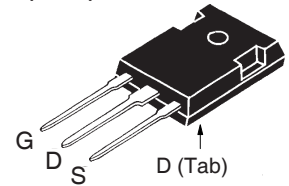
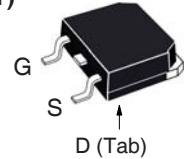


**Depletion Mode  
MOSFET**
**IXTH10N100D2  
IXTT10N100D2**

$$V_{DSX} = 1000V$$

$$I_{D(on)} \geq 10A$$

$$R_{DS(on)} \leq 1.5\Omega$$

**N-Channel**

**TO-247 (IXTH)**

**TO-268 (IXTT)**


G = Gate      D = Drain  
S = Source    Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSX}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1000	V
$V_{DGX}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GS} = 1M\Omega$	1000	V
$V_{GSX}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$P_D$	$T_C = 25^\circ\text{C}$	695	W
$T_J$		- 55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		- 55 ... +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
$M_d$	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSX}$	$V_{GS} = -5V, I_D = 250\mu\text{A}$	1000		V
$V_{GS(off)}$	$V_{DS} = 25V, I_D = 1\text{mA}$	- 2.5		V
$I_{GSX}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$ nA
$I_{DSX(off)}$	$V_{DS} = V_{DSX}, V_{GS} = -5V$ $T_J = 125^\circ\text{C}$			10 $\mu\text{A}$ 250 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 0V, I_D = 5A, \text{ Note 1}$			1.5 $\Omega$
$I_{D(on)}$	$V_{GS} = 0V, V_{DS} = 25V, \text{ Note 1}$	10		A

**Features**

- Normally ON Mode
- International Standard Packages
- Molding Epoxies Meet UL94V-0 Flammability Classification

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- Audio Amplifiers
- Start-up Circuits
- Protection Circuits
- Ramp Generators
- Current Regulators
- Active Loads

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 30\text{V}$ , $I_D = 5\text{A}$ , Note 1	11	17	S
$C_{iss}$	$V_{GS} = -10\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		5320	pF
$C_{oss}$			300	pF
$C_{rss}$			70	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = \pm 5\text{V}$ , $V_{DS} = 500\text{V}$ , $I_D = 5\text{A}$ $R_G = 3.3\Omega$ (External)		33	ns
$t_r$			36	ns
$t_{d(off)}$			33	ns
$t_f$			164	ns
$Q_{g(on)}$	$V_{GS} = \pm 5\text{V}$ , $V_{DS} = 500\text{V}$ , $I_D = 5\text{A}$		200	nC
$Q_{gs}$			19	nC
$Q_{gd}$			98	nC
$R_{thJC}$	TO-247			0.18 $^\circ\text{C/W}$
$R_{thCS}$			0.21	$^\circ\text{C/W}$

### Safe-Operating-Area Specification

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 800\text{V}$ , $I_D = 0.22\text{A}$ , $T_C = 75^\circ\text{C}$ , $t_p = 5\text{s}$	176		W

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{SD}$	$I_F = 10\text{A}$ , $V_{GS} = -10\text{V}$ , Note 1		0.8	1.3 V
$t_{rr}$	$I_F = 5\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$ , $V_{GS} = -10\text{V}$		1.2	$\mu\text{s}$
$I_{RM}$			23	A
$Q_{RM}$			13.8	$\mu\text{C}$

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

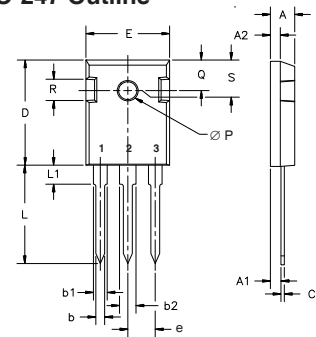
### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2  
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

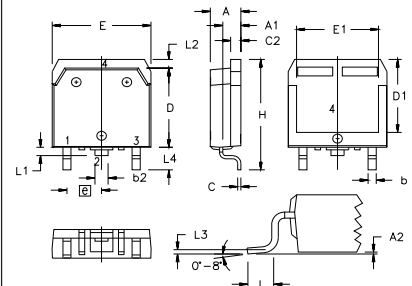
### TO-247 Outline



Terminals: 1 - Gate 2 - Drain  
3 - Source

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L <sub>1</sub>		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

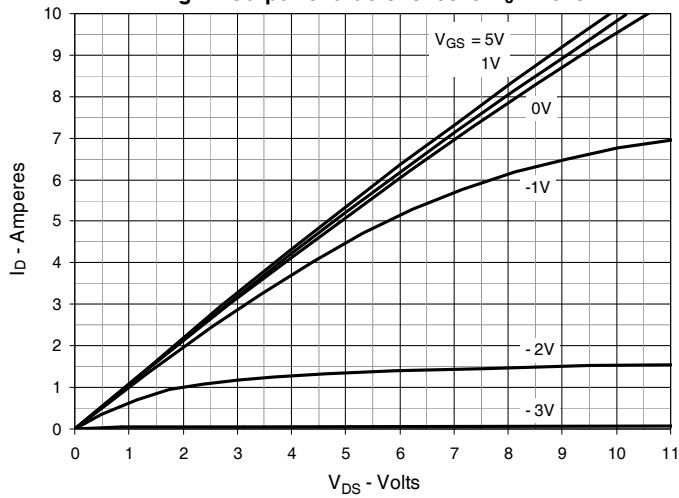
### TO-268 Outline



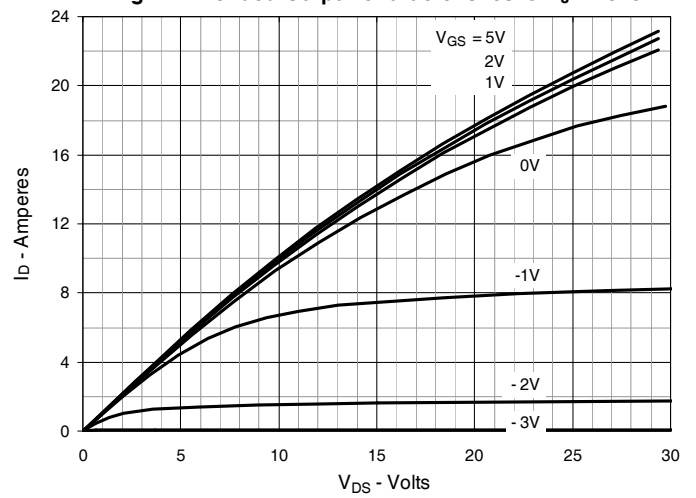
Terminals: 1 - Gate 2,4 - Drain  
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A <sub>1</sub>	.106	.114	2.70	2.90
A <sub>2</sub>	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b <sub>2</sub>	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C <sub>2</sub>	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D <sub>1</sub>	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E <sub>1</sub>	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L <sub>1</sub>	.047	.055	1.20	1.40
L <sub>2</sub>	.039	.045	1.00	1.15
L <sub>3</sub>	.010	BSC	0.25	BSC
L <sub>4</sub>	.150	.161	3.80	4.10

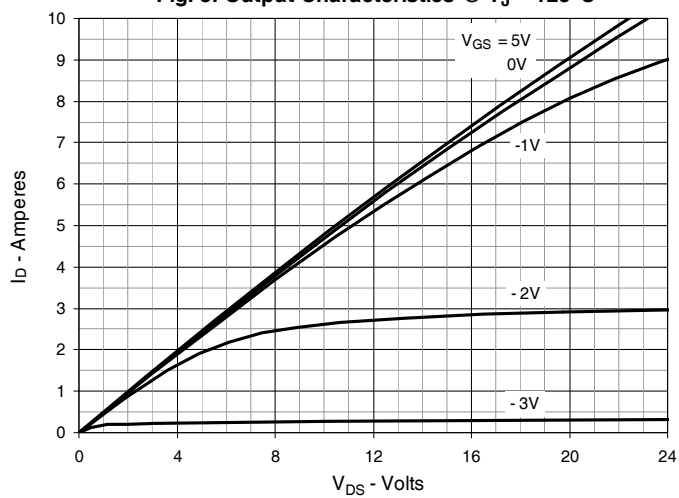
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



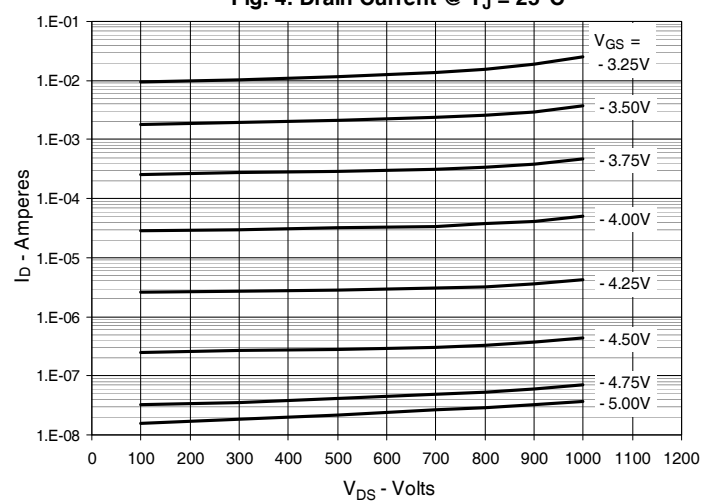
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



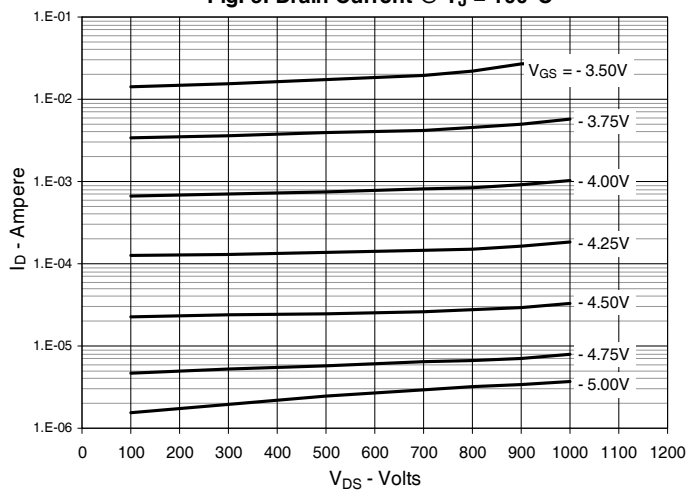
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



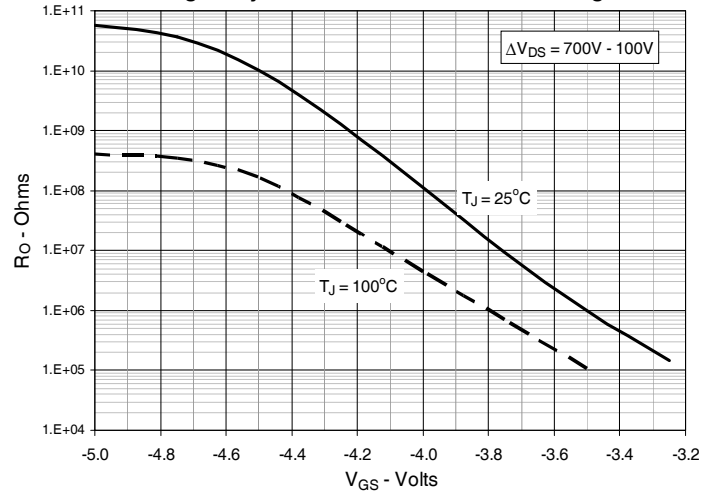
**Fig. 4. Drain Current @  $T_J = 25^\circ\text{C}$**



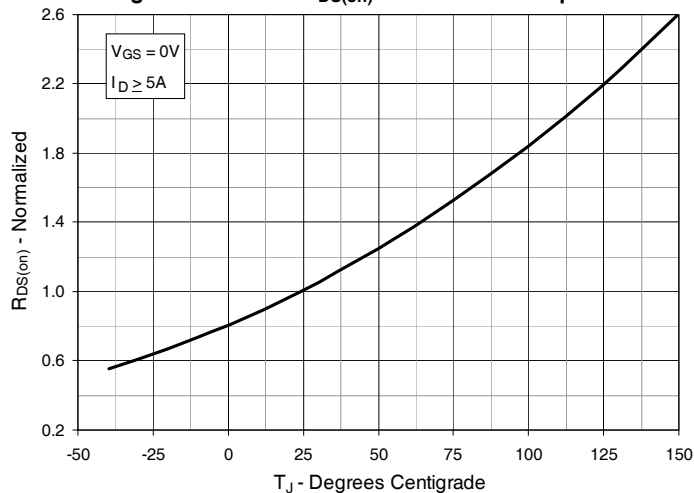
**Fig. 5. Drain Current @  $T_J = 100^\circ\text{C}$**



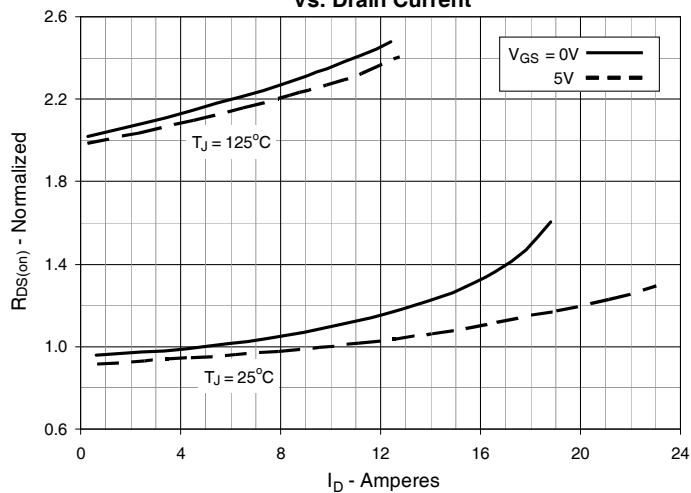
**Fig. 6. Dynamic Resistance vs. Gate Voltage**



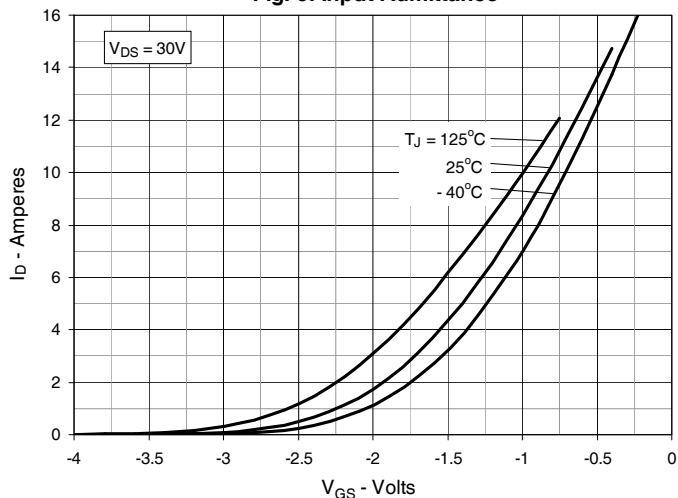
**Fig. 7. Normalized  $R_{DS(on)}$  vs. Junction Temperature**



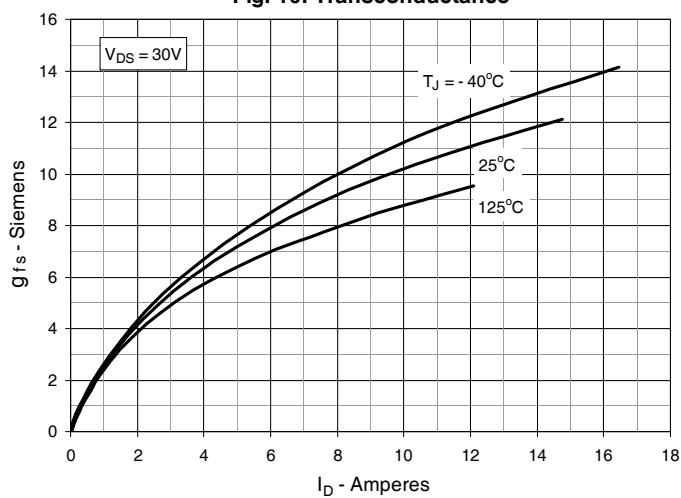
**Fig. 8.  $R_{DS(on)}$  Normalized to  $I_D = 5A$  Value vs. Drain Current**



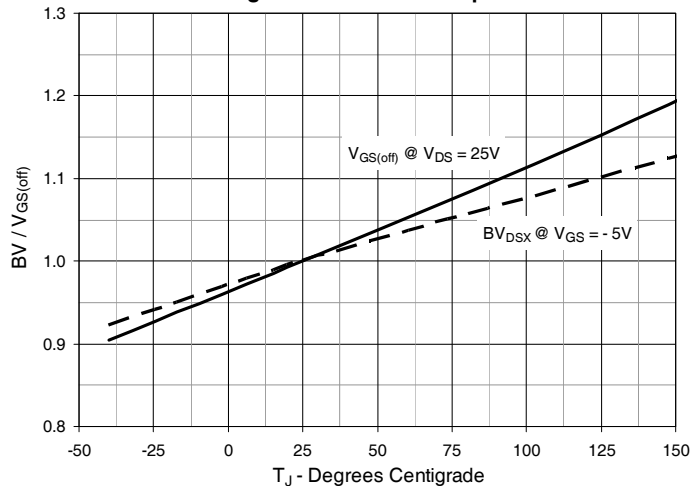
**Fig. 9. Input Admittance**



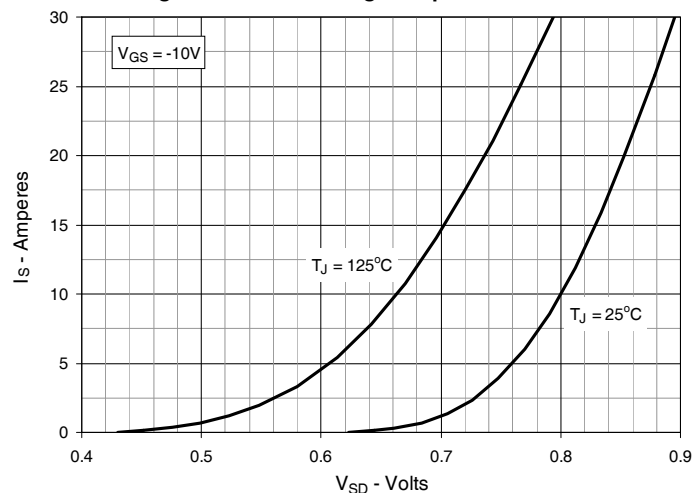
**Fig. 10. Transconductance**



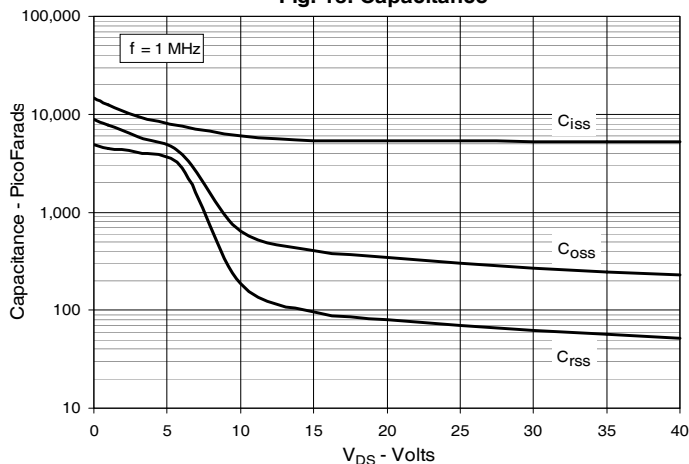
**Fig. 11. Normalized Breakdown and Threshold Voltages vs. Junction Temperature**



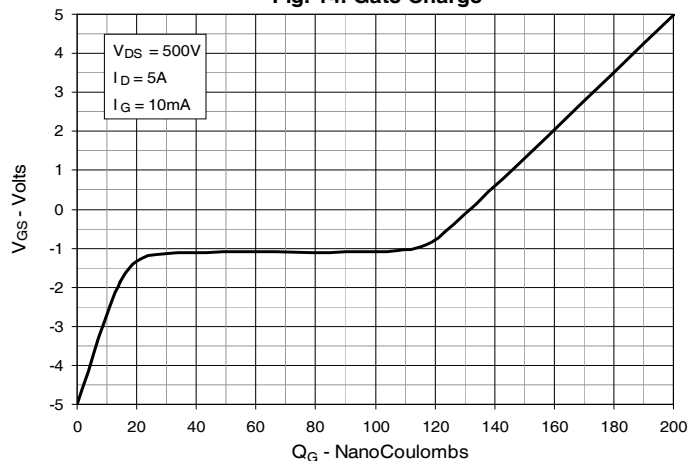
**Fig. 12. Forward Voltage Drop of Intrinsic Diode**



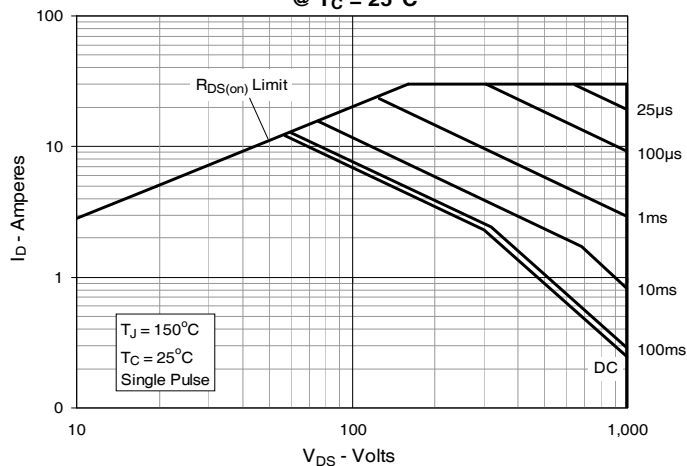
**Fig. 13. Capacitance**



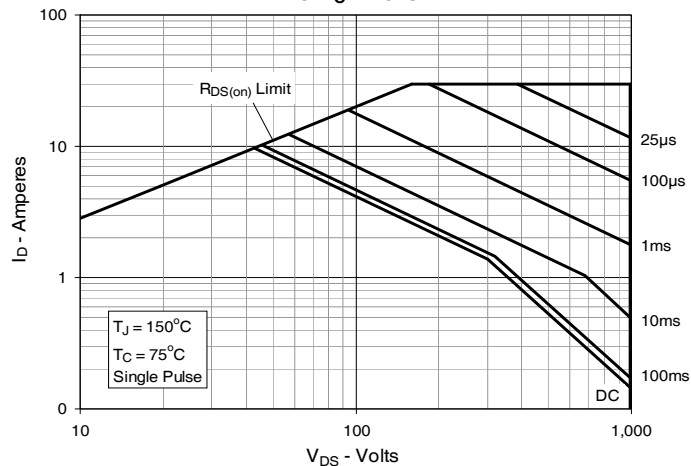
**Fig. 14. Gate Charge**



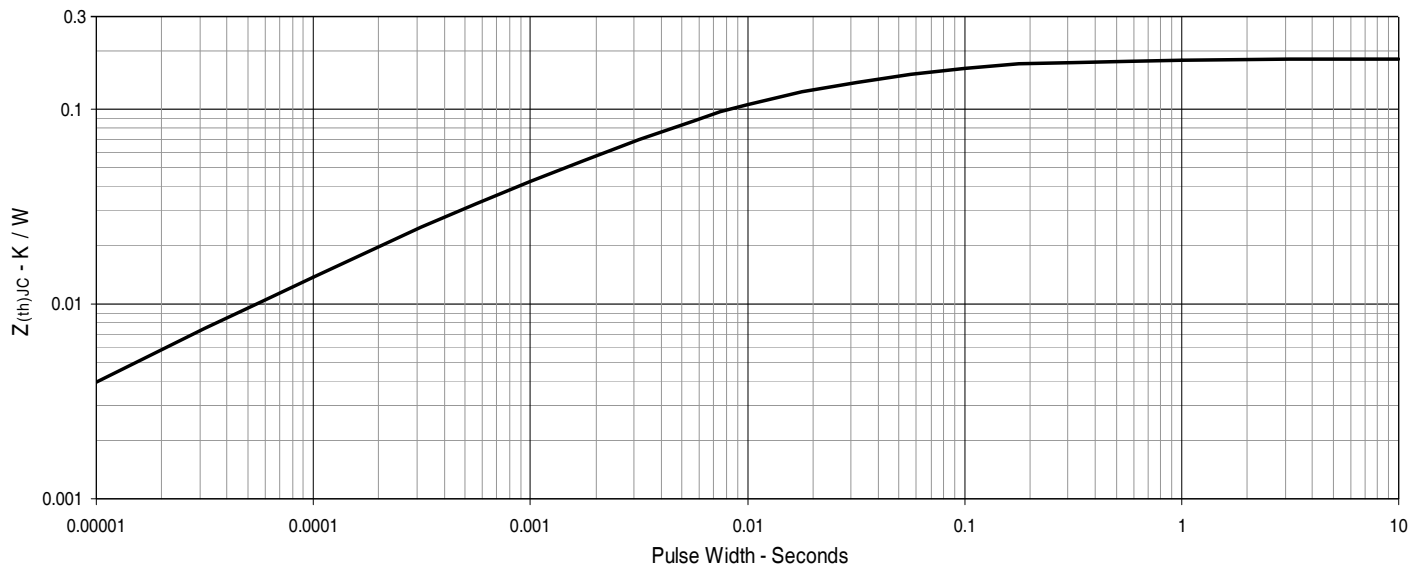
**Fig. 15. Forward-Bias Safe Operating Area @  $T_C = 25^\circ\text{C}$**



**Fig. 16. Forward-Bias Safe Operating Area @  $T_C = 75^\circ\text{C}$**



**Fig. 17. Maximum Transient Thermal Impedance**





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